

## TPS51200-EP シンクソースDDR終端レギュレータ

### 1 特長

- 入力電圧: 2.5Vレールと3.3Vレールをサポート
- VLDOIN電圧範囲: 1.1V~3.5V
- シンクソース終端レギュレータにドループ補正を内蔵
- メモリ終端アプリケーション(DDR)に必要な最低出力容量20 $\mu$ F (通常は3 $\times$ 10 $\mu$ F MLCC)
- PGOODによる出力レギュレーション監視
- EN入力
- REFIN入力により、直接または分圧抵抗経由で入力を柔軟にトラッキング可能
- リモート・センシング(VOSNS)
- $\pm$ 10mAのバッファ付きリファレンス(REFOUT)
- ソフトスタート、UVLO、OCLを内蔵
- サーマル・シャットダウン
- DDRおよびDDR2 JEDEC仕様に準拠
- DDR3、低消費電力DDR3、およびDDR4 VTTアプリケーションをサポート
- サーマル・パッド付き10ピンVSONパッケージ
- 防衛、航空宇宙、および医療アプリケーションをサポート
  - 管理されたベースライン
  - 単一のアセンブリ/テスト施設
  - 単一の製造施設
  - 軍用温度範囲(-55 $^{\circ}$ C~125 $^{\circ}$ C)で利用可能
  - 長期にわたる製品ライフ・サイクル
  - 製品変更通知の延長
  - 製品のトレーサビリティ

### 2 アプリケーション

- DDR、DDR2、DDR3、低消費電力DDR3、DDR4用のメモリ終端レギュレータ
- ノートPC、デスクトップPC、サーバー
- テレコムおよびデータコム
- 基地局
- LCD-TVおよびPDP-TV
- 複写機およびプリンタ
- セットトップ・ボックス

### 3 概要

TPS51200-EPデバイスは、シンクソースのダブル・データ・レート(DDR)終端レギュレータで、低入力電圧、低コスト、低ノイズで省スペースが重要なシステム向けに設計されています。

TPS51200-EPは高速な過渡応答特性を持ち、必要な最小出力容量はわずか20 $\mu$ Fです。TPS51200-EPはリモート・センシング機能と、DDR、DDR2、DDR3、低消費電力DDR3、DDR4 VTTバス終端のすべての電力要件をサポートします。

また、TPS51200-EPはDDRアプリケーションに対して、出力レギュレーションを監視するためのオープン・ドレインPGOOD信号と、S3 (RAMへのサスペンド)時にVTTを放電するために使用可能なEN信号を提供します。

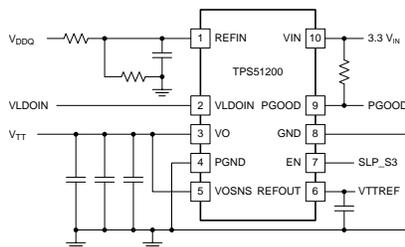
TPS51200-EPは熱効率の高い10ピンVSONサーマル・パッド・パッケージで供給され、グリーンおよび鉛フリーの両方の基準を満たしています。温度定格は-55 $^{\circ}$ C~+125 $^{\circ}$ Cです。

#### 製品情報(1)

型番	パッケージ	本体サイズ(公称)
TPS51200-EP	VSON (10)	3.00mm $\times$ 3.00mm

(1) 提供されているすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。

#### 単純化されたDDRアプリケーション



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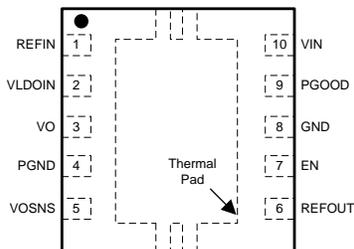
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## 4 改訂履歴

日付	改訂内容	注
2016年6月	*	初版

## 5 Pin Configuration and Functions

**DRC Package**  
**10-Pin VSON With Exposed Thermal Pad**  
**Top View**



### Pin Functions

PIN		I/O <sup>(1)</sup>	DESCRIPTION
NAME	NO.		
EN	7	I	For DDR VTT application, connect EN to SLP_S3. For any other application, use the EN pin as the ON/OFF function.
GND	8	G	Signal ground. Connect to negative terminal of the output capacitor.
PGND <sup>(2)</sup>	4	G	Power ground output for the LDO.
PGOOD	9	O	PGOOD output. Indicates regulation.
REFIN	1	I	Reference input.
REFOUT	6	O	Reference output. Connect to GND through 0.1- $\mu$ F ceramic capacitor.
VIN	10	I	2.5-V or 3.3-V power supply. A ceramic decoupling capacitor with a value between 1- $\mu$ F and 4.7- $\mu$ F is required.
VLDOIN	2	I	Supply voltage for the LDO.
VO	3	O	Power output for the LDO.
VOSNS	5	I	Voltage sense input for the LDO. Connect to positive terminal of the output capacitor or the load.

(1) I = Input, O = Output, G = Ground.

(2) Thermal pad connection. See [Figure 31](#) in the *Thermal Design Considerations* section for additional information.

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating junction temperature range (unless otherwise noted) <sup>(1)</sup>

		MIN	MAX	UNIT
Input voltage <sup>(2)</sup>	REFIN, VIN, VLDOIN, VOSNS	-0.3	3.6	V
	EN	-0.3	6.5	
	PGND to GND	-0.3	0.3	
Output voltage <sup>(2)</sup>	REFOUT, VO	-0.3	3.6	V
	PGOOD	-0.3	6.5	
Operating junction temperature, T <sub>J</sub>		-55	150	°C
Storage temperature, T <sub>stg</sub>		-55	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to the network ground terminal unless otherwise noted.

### 6.2 ESD Ratings

		VALUE	UNIT
V <sub>(ESD)</sub> Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	V
	Charged device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
Supply voltages	VIN	2.375		3.5	V
Voltage	EN, VLDOIN, VOSNS	-0.1		3.5	V
	REFIN	0.5		1.8	
	PGOOD, VO	-0.1		3.5	
	REFOUT	-0.1		1.8	
	PGND	-0.1		0.1	
Operating junction temperature, T <sub>J</sub>		-55		125	°C

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TPS51200-EP	UNIT
		DRC (VSON)	
		10 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	55.6	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	84.6	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	30	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	5.5	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	30.1	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	10.9	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.5 Electrical Characteristics

Over recommended junction temperature range,  $V_{VIN} = 3.3\text{ V}$ ,  $V_{VLDOIN} = 1.8\text{ V}$ ,  $V_{REFIN} = 0.9\text{ V}$ ,  $V_{VOSNS} = 0.9\text{ V}$ ,  $V_{EN} = V_{VIN}$ ,  $C_{OUT} = 3 \times 10\ \mu\text{F}$  and circuit shown in (unless otherwise noted)

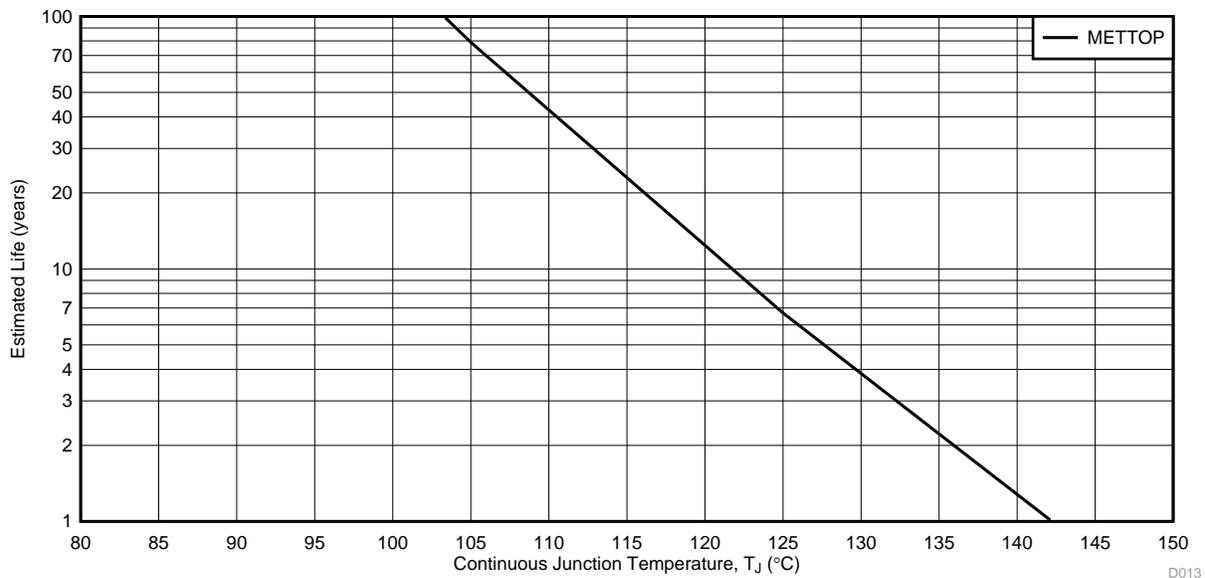
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>SUPPLY CURRENT</b>						
$I_{IN}$	Supply current	$T_J = 25\text{ }^\circ\text{C}$ , $V_{EN} = 3.3\text{ V}$ , no load		0.7	1	mA
$I_{IN(SDN)}$	Shutdown current	$T_J = 25\text{ }^\circ\text{C}$ , $V_{EN} = 0\text{ V}$ , $V_{REFIN} = 0$ , no load		65	80	$\mu\text{A}$
		$T_J = 25\text{ }^\circ\text{C}$ , $V_{EN} = 0\text{ V}$ , $V_{REFIN} > 0.4\text{ V}$ , no load		200	400	
$I_{LDOIN}$	Supply current of VLDOIN	$T_J = 25\text{ }^\circ\text{C}$ , $V_{EN} = 3.3\text{ V}$ , no load		1	50	$\mu\text{A}$
$I_{LDOIN(SDN)}$	Shutdown current of VLDOIN	$T_J = 25\text{ }^\circ\text{C}$ , $V_{EN} = 0\text{ V}$ , no load		0.1	50	$\mu\text{A}$
<b>INPUT CURRENT</b>						
$I_{REFIN}$	Input current, REFIN	$V_{EN} = 3.3\text{ V}$			1	$\mu\text{A}$
<b>VO OUTPUT</b>						
$V_{VOSNS}$	Output DC voltage, VO	$V_{REFOUT} = 1.25\text{ V}$ (DDR1), $I_O = 0\text{ A}$		1.25		V
				-15	15	mV
		$V_{REFOUT} = 0.9\text{ V}$ (DDR2), $I_O = 0\text{ A}$		0.9		V
				-15	15	mV
$V_{LDOIN} = 1.5\text{ V}$ , $V_{REFOUT} = 0.75\text{ V}$ (DDR3), $I_O = 0\text{ A}$		0.75		V		
		-15	15	mV		
$V_{VOTOL}$	Output voltage tolerance to REFOUT	$-2\text{ A} < I_{VO} < 2\text{ A}$	-25		25	mV
$I_{VOSRCL}$	VO source current Limit	With reference to REFOUT, $V_{OSNS} = 90\% \times V_{REFOUT}$	3		4.5	A
$I_{VOSNCL}$	VO sink current Limit	With reference to REFOUT, $V_{OSNS} = 110\% \times V_{REFOUT}$	3.5		5.5	A
$I_{DSCHRG}$	Discharge current, VO	$V_{REFIN} = 0\text{ V}$ , $V_{VO} = 0.3\text{ V}$ , $V_{EN} = 0\text{ V}$ , $T_J = 25\text{ }^\circ\text{C}$		18	25	$\Omega$
<b>POWERGOOD COMPARATOR</b>						
$V_{TH(PG)}$	VO PGOOD threshold	PGOOD window lower threshold with respect to REFOUT	-23.5%	-20%	-17.5%	
		PGOOD window upper threshold with respect to REFOUT	17.5%	20%	23.5%	
		PGOOD hysteresis		5%		
$t_{PGSTUPDLY}$	PGOOD start-up delay	Start-up rising edge, VOSNS within 15% of REFOUT		2		ms
$V_{PGOODLOW}$	Output low voltage	$I_{SINK} = 4\text{ mA}$			0.4	V
$t_{PBADDLY}$	PGOOD bad delay	VOSNS is outside of the $\pm 20\%$ PGOOD window		10		$\mu\text{s}$
$I_{PGOODLK}$	Leakage current <sup>(1)</sup>	$V_{OSNS} = V_{REFIN}$ (PGOOD high impedance), $V_{PGOOD} = V_{VIN} + 0.2\text{ V}$			1	$\mu\text{A}$
<b>REFIN AND REFOUT</b>						
$V_{REFIN}$	REFIN voltage range		0.5		1.8	V
$V_{REFINUVLO}$	REFIN undervoltage lockout	REFIN rising	360	390	420	mV
$V_{REFINUVHYS}$	REFIN undervoltage lockout hysteresis			20		mV
$V_{REFOUT}$	REFOUT voltage			REFIN		V
$V_{REFOUTTOL}$	REFOUT voltage tolerance to $V_{REFIN}$	$-10\text{ mA} < I_{REFOUT} < 10\text{ mA}$ , $V_{REFIN} = 1.25\text{ V}$	-15		15	mV
		$-10\text{ mA} < I_{REFOUT} < 10\text{ mA}$ , $V_{REFIN} = 0.9\text{ V}$	-15		15	
		$-10\text{ mA} < I_{REFOUT} < 10\text{ mA}$ , $V_{REFIN} = 0.75\text{ V}$	-15		15	
		$-10\text{ mA} < I_{REFOUT} < 10\text{ mA}$ , $V_{REFIN} = 0.6\text{ V}$	-15		15	
$I_{REFOUTSRCL}$	REFOUT source current limit	$V_{REFOUT} = 0\text{ V}$	10	40		mA
$I_{REFOUTSNCL}$	REFOUT sink current limit	$V_{REFOUT} = 0\text{ V}$	10	40		mA

(1) Ensured by design. Not production tested.

### Electrical Characteristics (continued)

Over recommended junction temperature range,  $V_{VIN} = 3.3\text{ V}$ ,  $V_{VLDOIN} = 1.8\text{ V}$ ,  $V_{REFIN} = 0.9\text{ V}$ ,  $V_{VOSNS} = 0.9\text{ V}$ ,  $V_{EN} = V_{VIN}$ ,  $C_{OUT} = 3 \times 10\ \mu\text{F}$  and circuit shown in (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>UVLO AND EN LOGIC THRESHOLD</b>					
$V_{VINUVIN}$ UVLO threshold	Wake up, $T_J = 25^\circ\text{C}$	2.2	2.3	2.375	V
	Hysteresis		50		mV
$V_{ENIH}$ High-level input voltage	Enable	1.7			V
$V_{ENIL}$ Low-level input voltage	Enable			0.3	V
$V_{ENYST}$ Hysteresis voltage	Enable		0.5		V
$I_{ENLEAK}$ Logic input leakage current	EN, $T_J = 25^\circ\text{C}$	-1		1	$\mu\text{A}$
<b>THERMAL SHUTDOWN</b>					
$T_{SON}$ Thermal shutdown threshold <sup>(1)</sup>	Shutdown temperature		150		$^\circ\text{C}$
	Hysteresis		25		

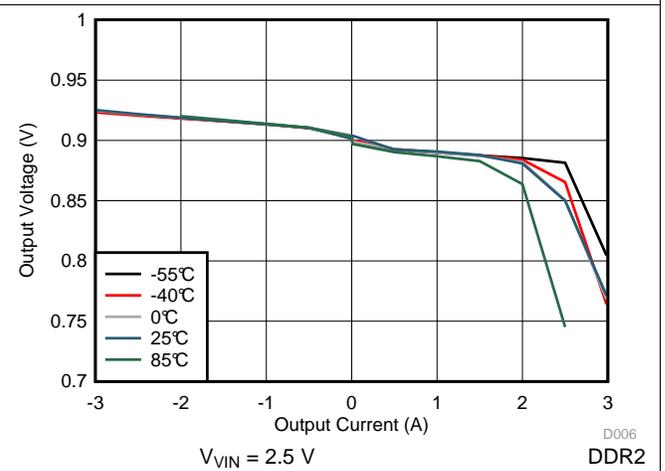
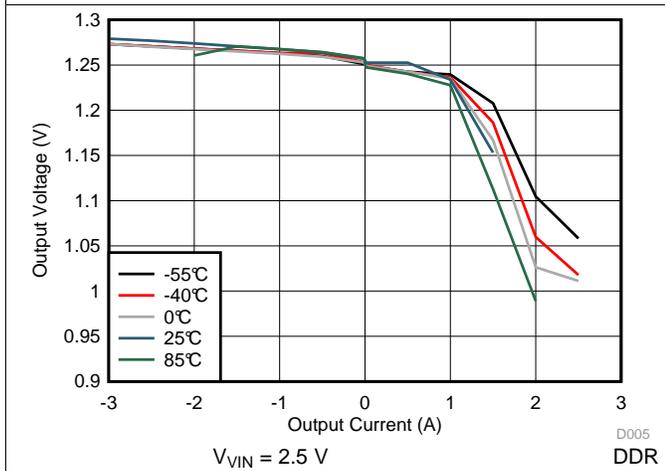
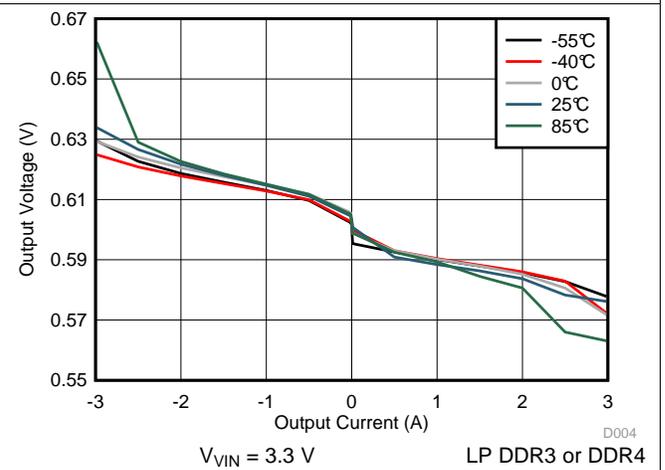
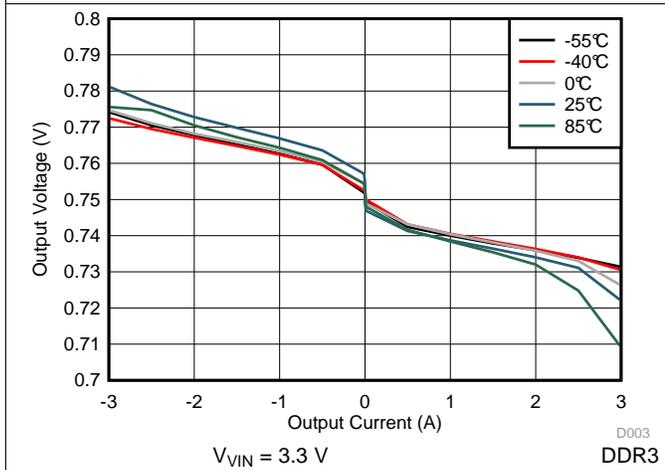
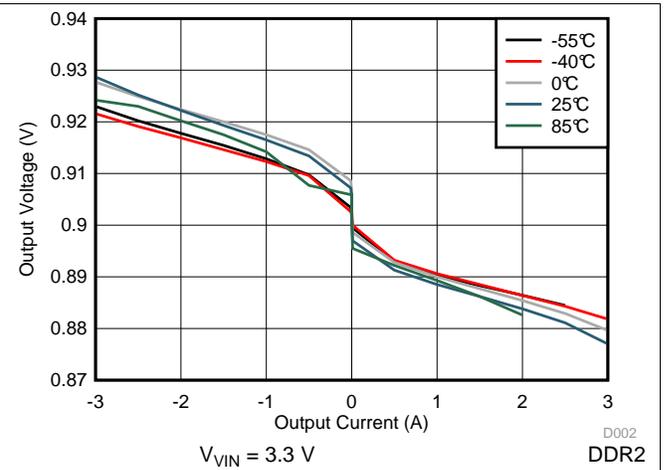
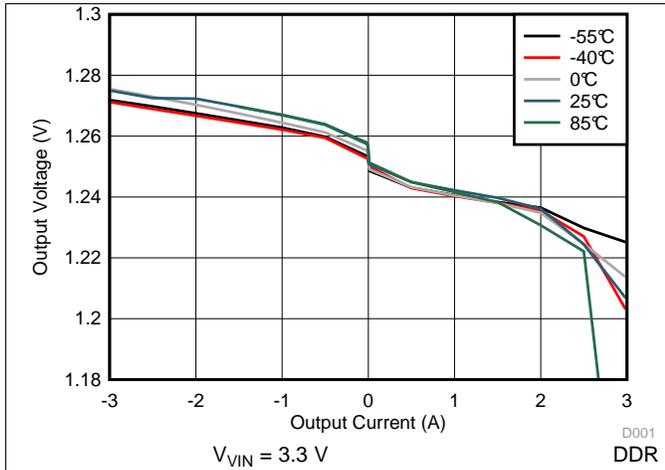


- (1) Electromigration fail mode = time at temperature with bias.
- (2) Silicon operating life design goal is 10 years at 105°C junction temperature (does not include package interconnect life).
- (3) The predicted operating lifetime versus junction temperature is based on reliability modeling and available qualification data.

**Figure 1. Predicted Lifetime Derating Chart for TPS51200-EP**

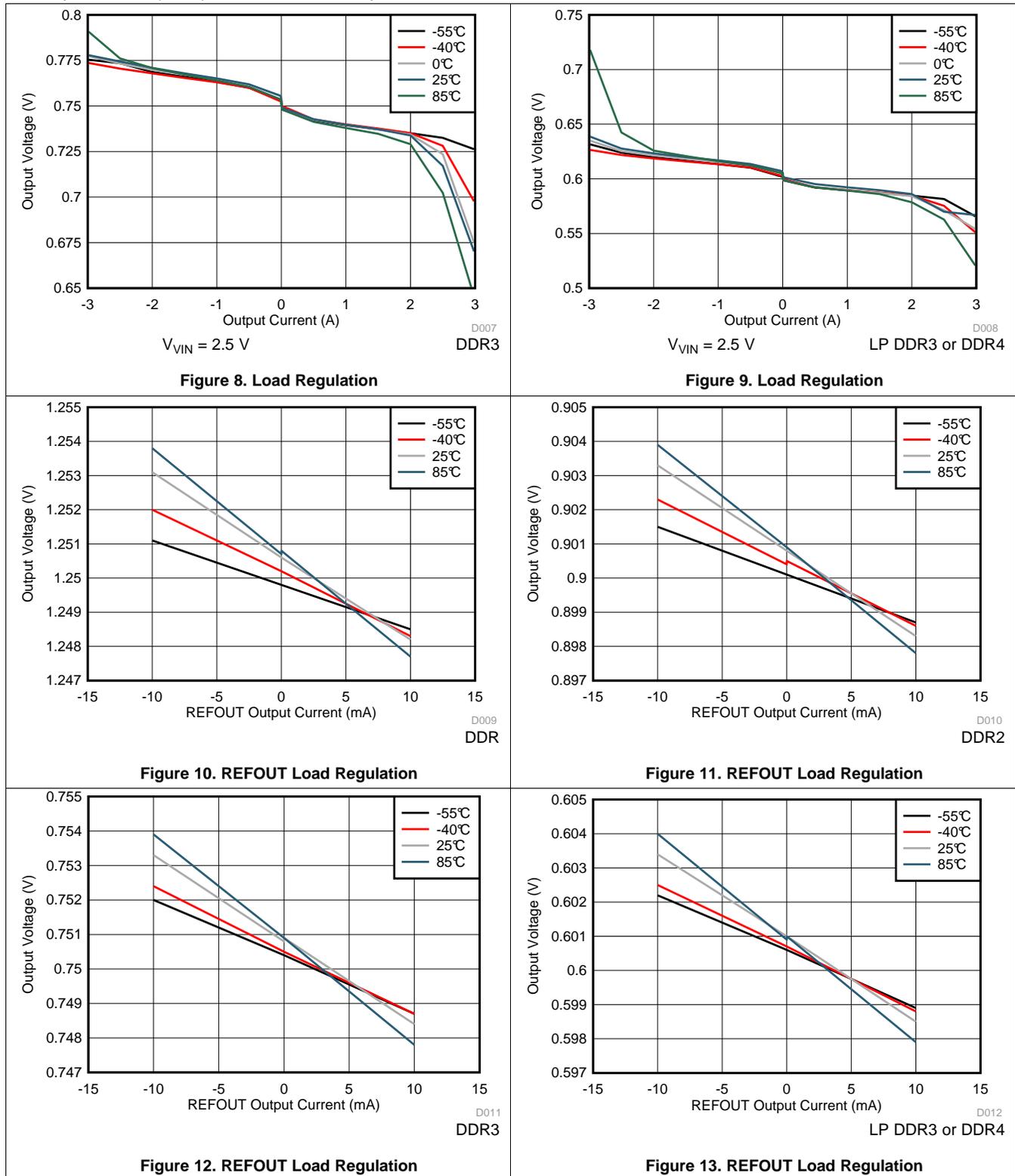
## 6.6 Typical Characteristics

3 × 10-μF MLCCs (0805) are used on the output.



Typical Characteristics (continued)

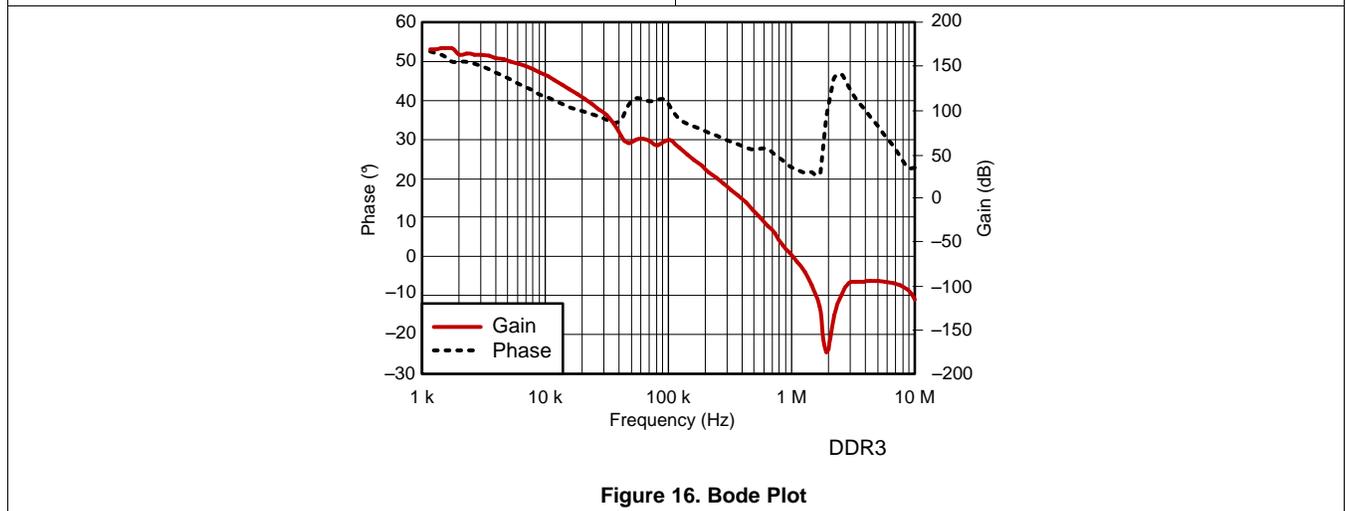
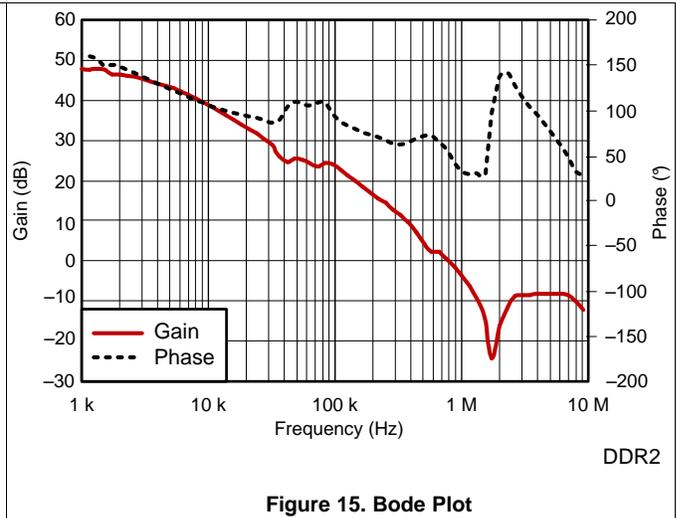
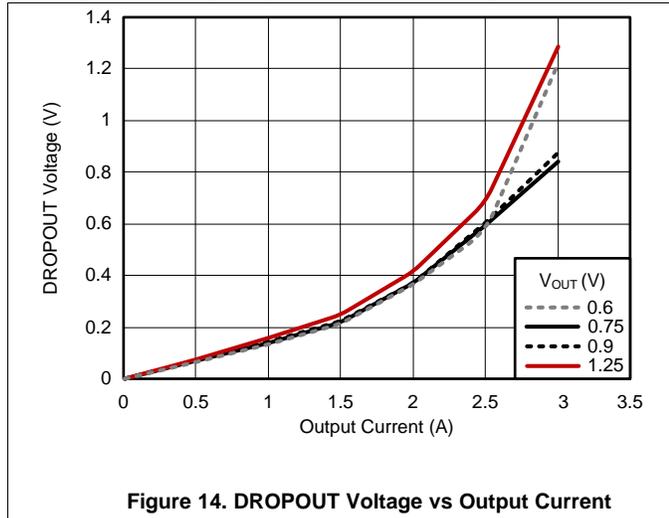
3 × 10-μF MLCCs (0805) are used on the output.





**Typical Characteristics (continued)**

3 × 10-μF MLCCs (0805) are used on the output.



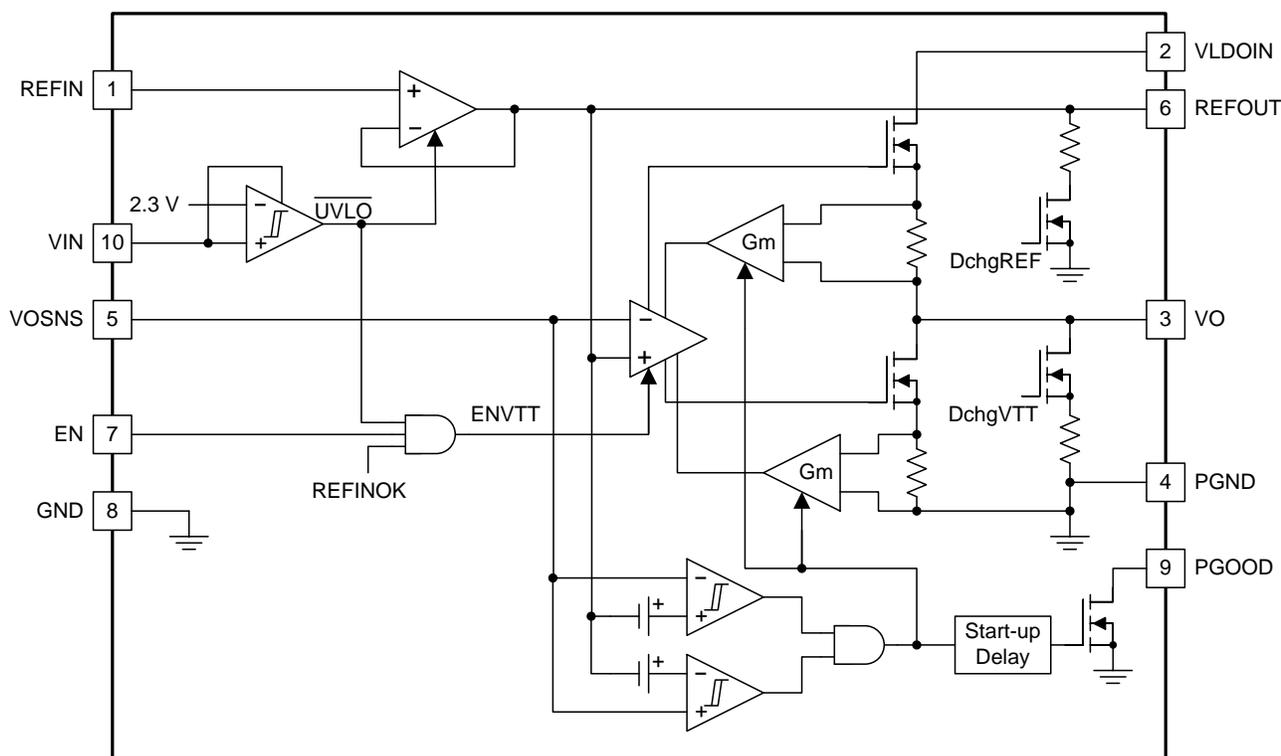
## 7 Detailed Description

### 7.1 Overview

The TPS51200-EP device is a sink and source double data rate (DDR) termination regulator specifically designed for low-input voltage, low-cost, low-noise systems where space is a key consideration.

The device maintains a fast transient response and only requires a minimum output capacitance of 20  $\mu\text{F}$ . The device supports a remote sensing function and all power requirements for DDR, DDR2, DDR3, Low-Power DDR3, and DDR4 VTT bus termination.

### 7.2 Functional Block Diagram



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### 7.3 Feature Description

#### 7.3.1 Sink and Source Regulator (VO Pin)

The TPS51200-EP is a sink and source tracking termination regulator specifically designed for low-input voltage, low-cost, and low-external component count systems where space is a key application parameter. The device integrates a high-performance, low-dropout (LDO) linear regulator that is capable of both sourcing and sinking current. The LDO regulator employs a fast feedback loop so that small ceramic capacitors can be used to support the fast load transient response. To achieve tight regulation with minimum effect of trace resistance, connect a remote sensing terminal, VOSNS, to the positive terminal of each output capacitor as a separate trace from the high-current path from VO.

#### 7.3.2 Reference Input (REFIN Pin)

The output voltage, VO, is regulated to REFOUT. When REFIN is configured for standard DDR termination applications, REFIN can be set by an external equivalent ratio voltage divider connected to the memory supply bus (VDDQ). The TPS51200-EP device supports REFIN voltages from 0.5 V to 1.8 V, making it versatile and ideal for many types of low-power LDO applications.

## Feature Description (continued)

### 7.3.3 Reference Output (REFOUT Pin)

When it is configured for DDR termination applications, REFOUT generates the DDR VTT reference voltage for the memory application. It is capable of supporting both a sourcing and sinking load of 10 mA. REFOUT becomes active when REFIN voltage rises to 0.39 V and VIN is above the UVLO threshold. When REFOUT is less than 0.375 V, it is disabled and subsequently discharges to GND through an internal 10-kΩ MOSFET. REFOUT is independent of the EN pin state.

### 7.3.4 Soft-Start Sequencing

A current clamp implements the soft-start function of the VO pin. The current clamp allows the output capacitors to be charged with low and constant current, providing a linear ramp-up of the output voltage. When VO is outside of the powergood (PGOOD) window, the current clamp level is one-half of the full overcurrent limit (OCL) level. When VO rises or falls within the PGOOD window, the current clamp level switches to the full OCL level. The soft-start function is completely symmetrical and the overcurrent limit works for both directions. The soft-start function works not only from GND to the REFOUT voltage, but also from VLDOIN to the REFOUT voltage.

### 7.3.5 Enable Control (EN Pin)

When EN is driven high, the VO regulator begins normal operation. When the device drives EN low, VO discharges to GND through an internal 18-Ω MOSFET. REFOUT remains on when the device drives EN low. Ensure that the EN pin voltage remains lower than or equal to  $V_{VIN}$  at all times.

### 7.3.6 Powergood Function (PGOOD Pin)

The TPS51200-EP device provides an open-drain PGOOD output that goes high when the VO output is within  $\pm 20\%$  of REFOUT. PGOOD de-asserts within 10  $\mu$ s after the output exceeds the size of the PGOOD window. During initial VO start-up, PGOOD asserts high 2 ms (typ) after the VO enters PGOOD window. Because PGOOD is an open-drain output, a pull-up resistor with a value between 1 kΩ and 100 kΩ, placed between PGOOD and a stable active supply voltage rail, is required.

### 7.3.7 Current Protection (VO Pin)

The LDO has a constant overcurrent limit (OCL). The OCL level reduces by one-half when the output voltage is not within the PGOOD window. This reduction is a non-latch protection.

### 7.3.8 UVLO Protection (VIN Pin)

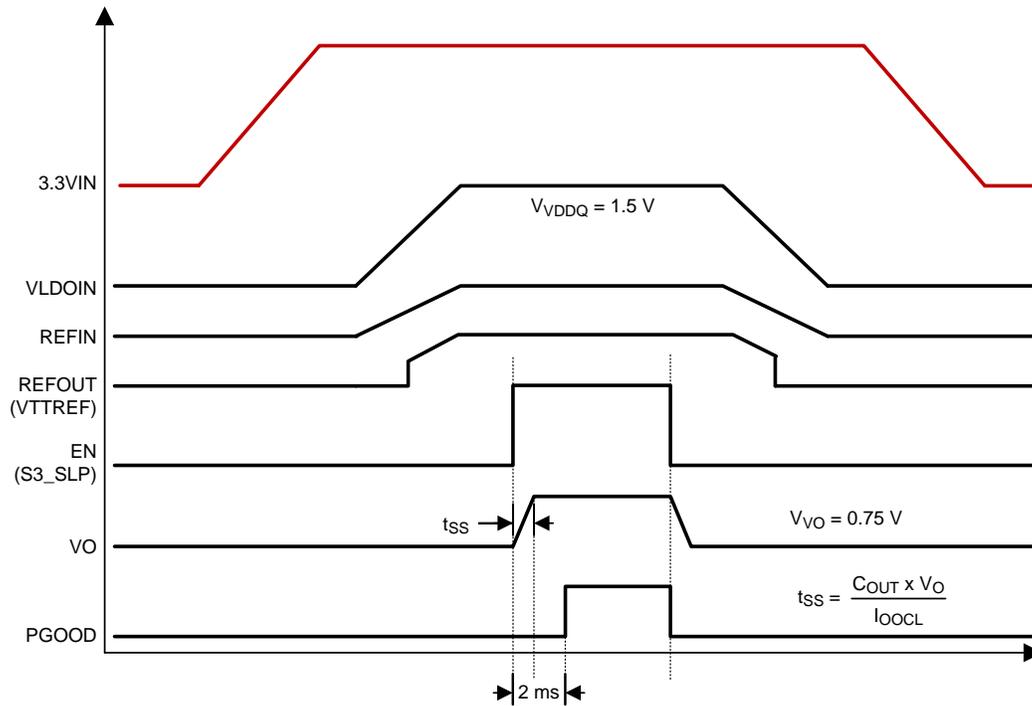
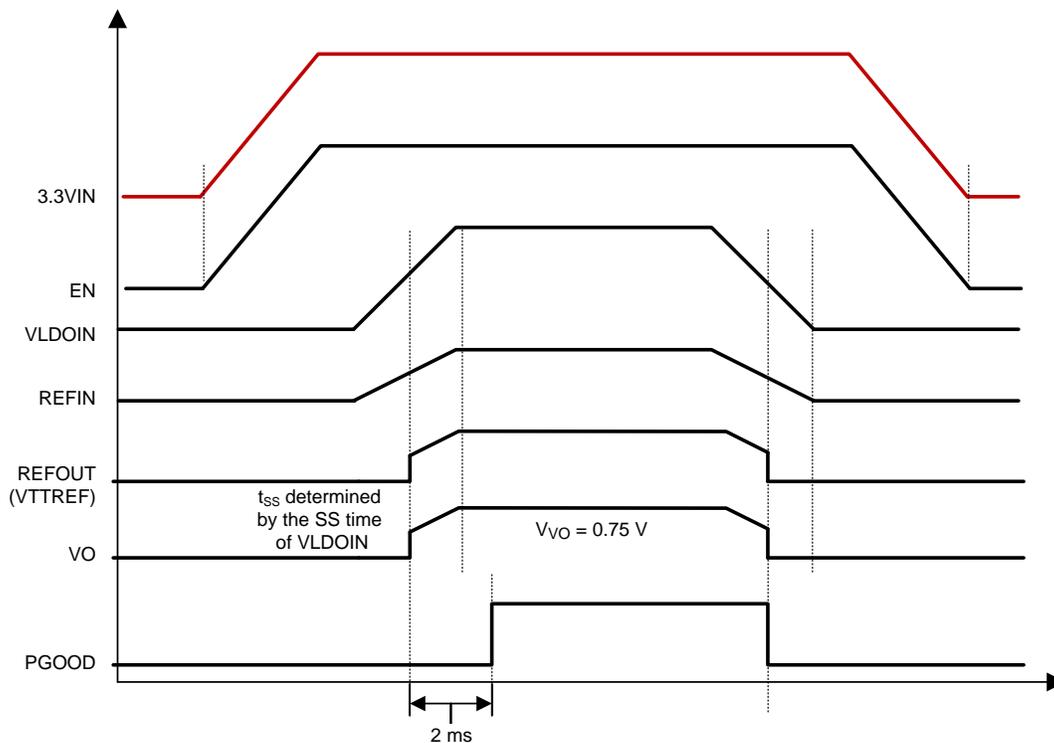
For VIN undervoltage lockout (UVLO) protection, the TPS51200-EP monitors VIN voltage. When the VIN voltage is lower than the UVLO threshold voltage, both the VO and REFOUT regulators are powered off. This shutdown is a non-latch protection.

### 7.3.9 Thermal Shutdown

The TPS51200-EP monitors junction temperature. If the device junction temperature exceeds the threshold value, (typically 150°C), the VO and REFOUT regulators both shut off, discharged by the internal discharge MOSFETs. This shutdown is a non-latch protection.

### 7.3.10 Tracking Start-up and Shutdown

The TPS51200-EP also supports tracking start-up and shutdown when the EN pin is tied directly to the system bus and not used to turn on or turn off the device. During tracking start-up, VO follows REFOUT once REFIN voltage is greater than 0.39 V. REFIN follows the rise of VDDQ rail through a voltage divider. The typical soft-start time ( $t_{SS}$ ) for the VDDQ rail is approximately 3 ms, however it may vary depending on the system configuration. The soft-start time of the VO output no longer depends on the OCL setting, but it is a function of the soft-start time of the VDDQ rail. PGOOD is asserted 2 ms after  $V_{VO}$  is within  $\pm 20\%$  of REFOUT. During tracking shutdown, the VO pin voltage falls following REFOUT until REFOUT reaches 0.37 V. When REFOUT falls below 0.37 V, the internal discharge MOSFETs turn on and quickly discharge both REFOUT and VO to GND. PGOOD is deasserted once VO is beyond the  $\pm 20\%$  range of REFOUT. [Figure 18](#) shows the typical timing diagram for an application that uses tracking start-up and shutdown.

**Feature Description (continued)**

**Figure 17. Typical Timing Diagram for S3 and Pseudo-S5 Support**

**Figure 18. Typical Timing Diagram of Tracking Start-up and Shutdown**

## 7.4 Device Functional Modes

### 7.4.1 Low-Input Voltage Applications

TPS51200-EP can be used in an application system that offers either a 2.5-V rail or a 3.3-V rail. If only a 5-V rail is available, consider using the [TPS51100](#) device as an alternative. The TPS51200-EP device has a minimum input voltage requirement of 2.375 V. If a 2.5-V rail is used, ensure that the absolute minimum voltage (both DC and transient) at the device pin is be 2.375 V or greater. The voltage tolerance for a 2.5-V rail input is between –5% and 5% accuracy, or better.

### 7.4.2 S3 and Pseudo-S5 Support

The TPS51200-EP provides S3 support by an EN function. The EN pin could be connected to an SLP\_S3 signal in the end application. Both REFOUT and VO are on when EN = high (S0 state). REFOUT is maintained while VO is turned off and discharged via an internal discharge MOSFET when EN = low (S3 state). When EN = low and the REFIN voltage is less than 0.39 V, TPS51200-EP enters pseudo-S5 state. Both VO and REFOUT outputs are turned off and discharged to GND through internal MOSFETs when pseudo-S5 support is engaged (S4 or S5 state). [Figure 17](#) shows a typical start-up and shutdown timing diagram for an application that uses S3 and pseudo-S5 support.

## 8 Application and Implementation

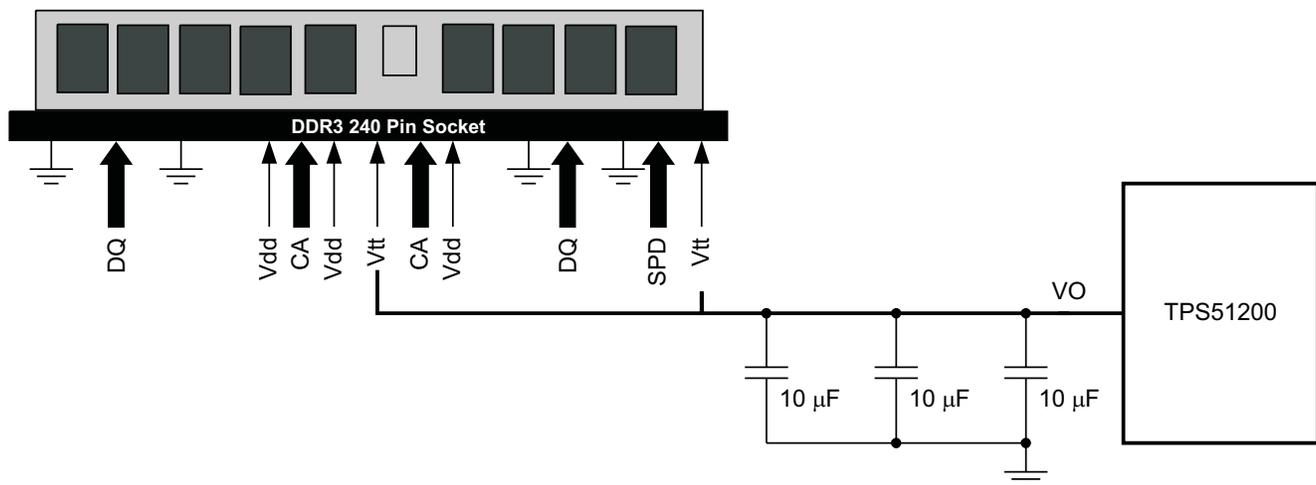
### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The TPS51200-EP device is specifically designed to power up the memory termination rail (as shown in Figure 19). The DDR memory termination structure determines the main characteristics of the VTT rail, which is to be able to sink and source current while maintaining acceptable VTT tolerance. See Figure 20 for typical characteristics for a single memory cell.

### 8.2 Typical VTT DIMM Applications



UDG-08022

**Figure 19. Typical Application Diagram for DDR3 VTT DIMM Using TPS51200-EP**

#### 8.2.1 Design Requirements

Use the information listed in Table 1 as the design parameters.

**Table 1. DDR, DDR2, DDR3, and LP DDR3 Termination Technology and Differences**

PARAMETER	DDR	DDR2	DR3	LOW-POWER DDR3
FSB data rates	200, 266, 333 and 400 MHz	400, 533, 677 and 800 MHz	800, 1066, 1330 and 1600 MHz	Same as DDR3
Termination	Motherboard termination to VTT for all signals	On-die termination for data group. VTT termination for address, command and control signals.	On-die termination for data group. VTT termination for address, command and control signals.	Same as DDR3
Termination current demand	Max sink and source transient currents of up to 2.6 A to 2.9 A	Not as demanding <ul style="list-style-type: none"> <li>• Only 34 signals (address, command, control) tied to VTT</li> <li>• ODT handles data signals</li> </ul> Less than 1 A of burst current	Not as demanding <ul style="list-style-type: none"> <li>• Only 34 signals (address, command, control) tied to VTT</li> <li>• ODT handles data signals</li> </ul> Less than 1 A of burst current	Same as DDR3
Voltage level	2.5-V core and I/O 1.25-V VTT	1.8-V core and I/O 0.9-V VTT	1.5-V core and I/O 0.75-V VTT	1.2-V core and I/O 0.6-V VTT

## 8.2.2 Detailed Design Procedure

### 8.2.2.1 Input Voltage Capacitor

Add a ceramic capacitor, with a value between 1- $\mu$ F and 4.7- $\mu$ F, placed close to the VIN pin, to stabilize the bias supply (2.5-V rail or 3.3-V rail) from any parasitic impedance from the supply.

### 8.2.2.2 VLDO Input Capacitor

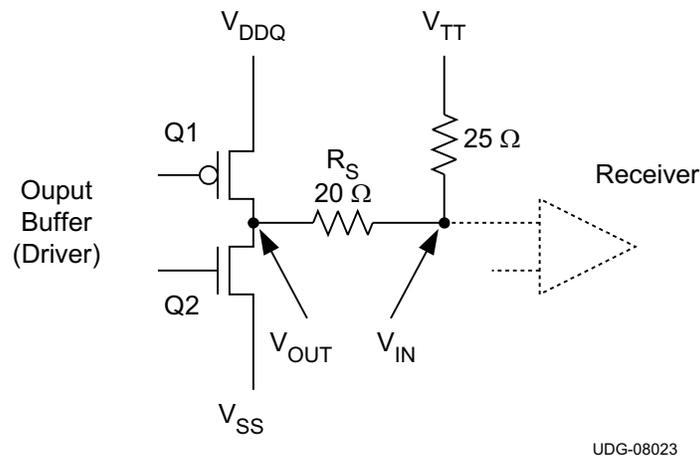
Depending on the trace impedance between the VLDOIN bulk power supply to the device, a transient increase of source current is supplied mostly by the charge from the VLDOIN input capacitor. Use a 10- $\mu$ F (or greater) ceramic capacitor to supply this transient charge. Provide more input capacitance as more output capacitance is used at the VO pin. In general, use one-half of the C<sub>OUT</sub> value for input.

### 8.2.2.3 Output Capacitor

For stable operation, the total capacitance of the VO output pin must be greater than 20  $\mu$ F. Attach 3  $\times$  10- $\mu$ F ceramic capacitors in parallel to minimize the effect of equivalent series resistance (ESR) and equivalent series inductance (ESL). If the ESR is greater than 2 m $\Omega$ , insert an RC filter between the output and the VOSNS input to achieve loop stability. The RC filter time constant should be almost the same as or slightly lower than the time constant of the output capacitor and its ESR.

### 8.2.2.4 Output Tolerance Consideration for VTT DIMM Applications

Figure 20 shows the typical characteristics for a single memory cell.



**Figure 20. DDR Physical Signal System Bi-Directional SSTL Signaling**

In Figure 20, when Q1 is on and Q2 is off:

- Current flows from VDDQ via the termination resistor to VTT
- VTT sinks current

In Figure 20, when Q2 is on and Q1 is off:

- Current flows from VTT via the termination resistor to GND
- VTT sources current

Because VTT accuracy has a direct impact on the memory signal integrity, it is imperative to understand the tolerance requirement on VTT. Equation 1 applies to both DC and AC conditions and is based on JEDEC VTT specifications for DDR and DDR2 (JEDEC standard: DDR JESD8-9B May 2002; DDR2 JESD8-15A Sept 2003).

$$V_{VTTREF} - 40 \text{ mV} < V_{VTT} < V_{VTTREF} + 40 \text{ mV} \quad (1)$$

The specification itself indicates that VTT must keep track of VTTREF for proper signal conditioning.

The TPS51200-EP ensures the regulator output voltage to be as shown in Equation 2, which applies to both DC and AC conditions.

$$V_{VTTREF} - 25 \text{ mV} < V_{VTT} < V_{VTTREF} + 25 \text{ mV}$$

where

$$\bullet \quad -2 \text{ A} < I_{VTT} < 2 \text{ A} \quad (2)$$

The regulator output voltage is measured at the regulator side, not the load side. The tolerance is applicable to DDR, DDR2, DDR3, Low Power DDR3, and DDR4 applications (see Table 1 for detailed information). To meet the stability requirement, a minimum output capacitance of 20  $\mu\text{F}$  is needed. Considering the actual tolerance on the MLCC capacitors,  $3 \times 10\text{-}\mu\text{F}$  ceramic capacitors sufficiently meet the VTT accuracy requirement.



The TPS51200-EP device uses transconductance ( $g_M$ ) to drive the LDO. The transconductance and output current of the device determine the voltage droop between the reference input and the output regulator. The typical transconductance level is 250 S at 2 A and changes with respect to the load in order to conserve the quiescent current (that is, the transconductance is very low at no load condition). The ( $g_M$ ) LDO regulator is a single pole system. Only the output capacitance determines the unity gain bandwidth for the voltage loop, as a result of the bandwidth nature of the transconductance (see [Equation 3](#)).

$$f_{UGBW} = \frac{g_M}{2 \times \pi \times C_{OUT}}$$

where

- $f_{UGBW}$  is the unity gain bandwidth
- $g_M$  is transconductance
- $C_{OUT}$  is the output capacitance

(3)

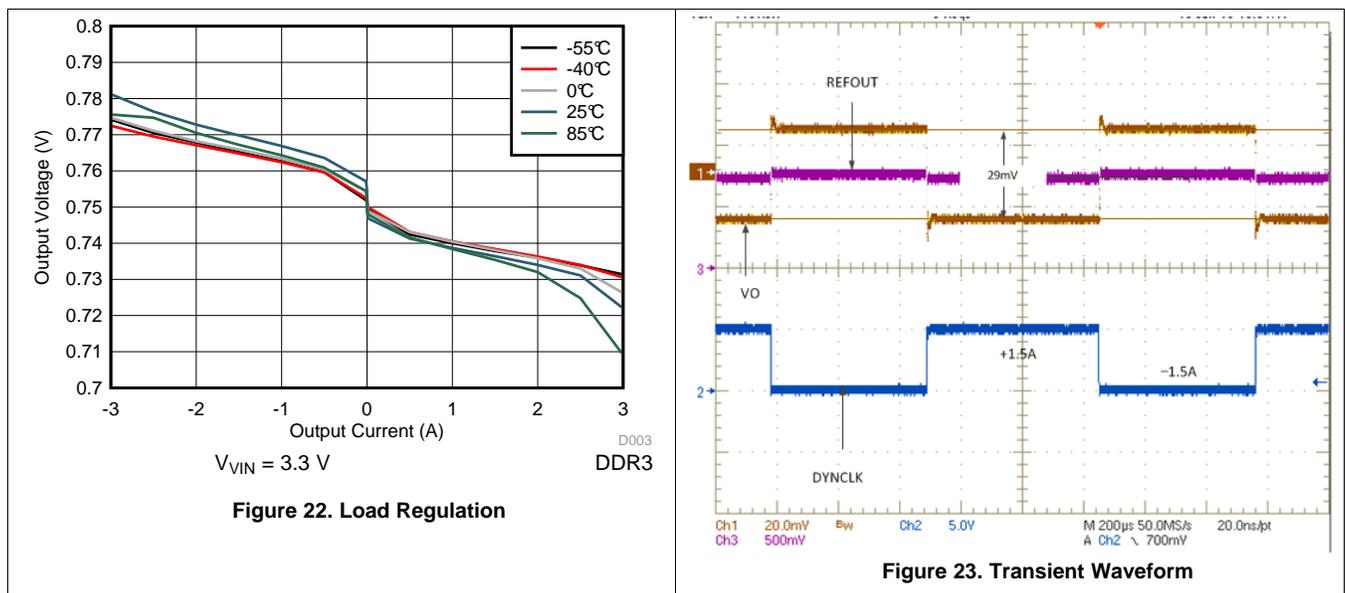
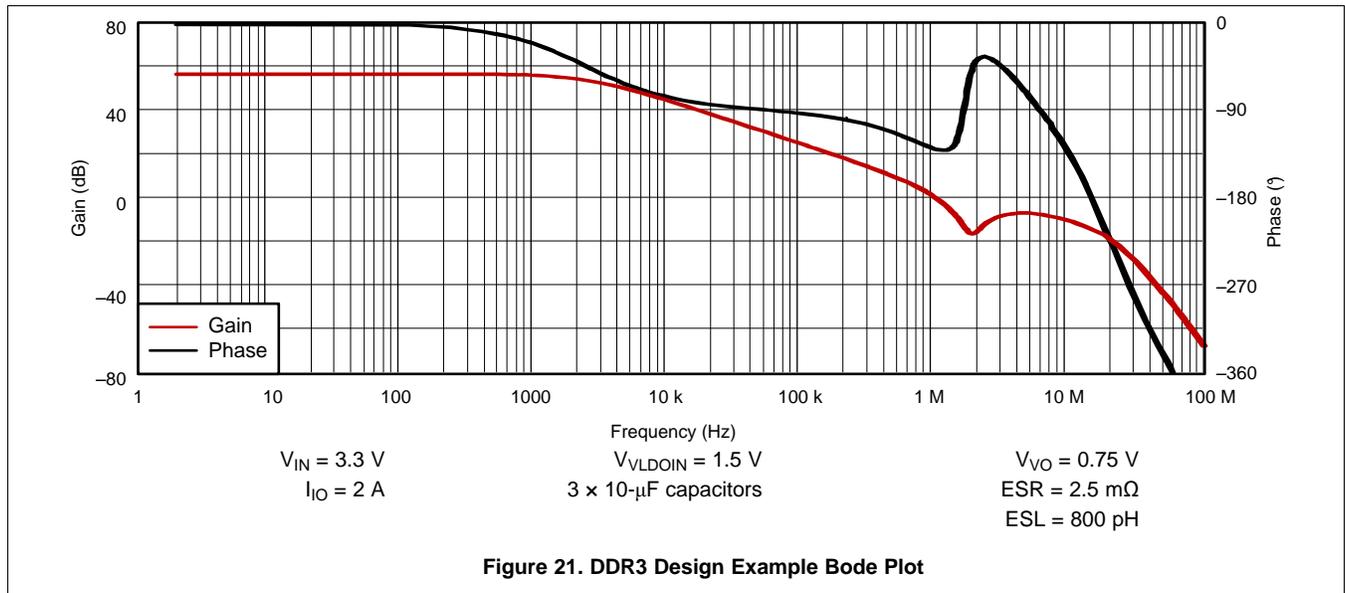
Consider these two limitations to this type of regulator that come from the output bulk capacitor requirement. In order to maintain stability, the zero location contributed by the ESR of the output capacitors must be greater than the –3-dB point of the current loop. This constraint means that higher ESR capacitors should not be used in the design. In addition, the impedance characteristics of the ceramic capacitor should be well understood in order to prevent the gain peaking effect around the transconductance ( $g_M$ ) –3-dB point because of the large ESL, the output capacitor, and the parasitic inductance of the VO pin voltage trace.

### 8.2.3 Application Curves

Figure 21 shows the bode plot simulation for this DDR3 design example of the TPS51200-EP device.

The unity-gain bandwidth is approximately 1 MHz and the phase margin is 52°. When the 0-dB level is crossed, the gain peaks because of the ESL effect. However, the peaking maintains a level well below 0 dB.

Figure 22 shows the load regulation and Figure 23 shows the transient response for a typical DDR3 configuration. When the regulator is subjected to ±1.5-A load step and release, the output voltage measurement shows no difference between the DC and AC conditions.



### 8.3 System Examples

#### 8.3.1 3.3-V<sub>IN</sub>, DDR2 Configuration

This design example describes a 3.3-V<sub>IN</sub>, DDR2 configuration application.

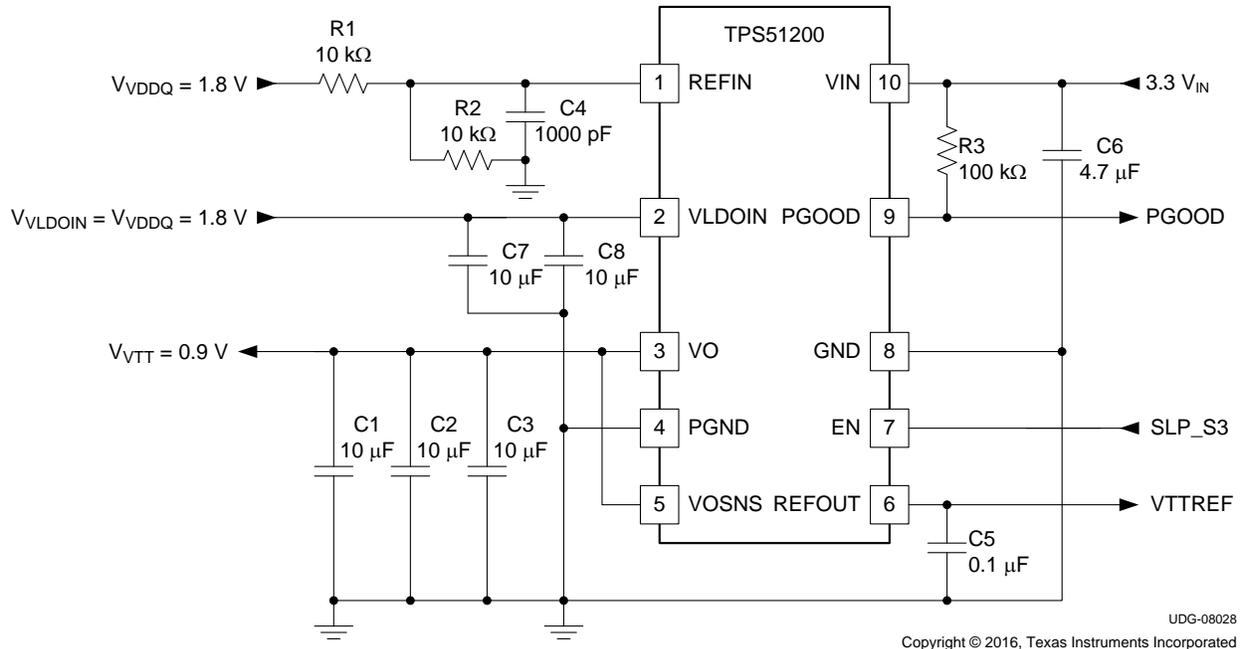


Figure 24. 3.3-V<sub>IN</sub>, DDR2 Configuration

Table 2. 3.3-V<sub>IN</sub>, DDR2 Configuration List of Materials

REFERENCE DESIGNATOR	DESCRIPTION	SPECIFICATION	PART NUMBER	MANUFACTURER
R1, R2	Resistor	10 kΩ		
R3		100 kΩ		
C1, C2, C3	Capacitor	10 μF, 6.3 V	GRM21BR70J106KE76L	Murata
C4		1000 pF		
C5		0.1 μF		
C6		4.7 μF, 6.3 V	GRM21BR60J475KA11L	Murata
C7, C8		10 μF, 6.3 V	GRM21BR70J106KE76L	Murata

### 8.3.2 2.5-V<sub>IN</sub>, DDR3 Configuration

This design example describes a 2.5-V<sub>IN</sub>, DDR3 configuration application.

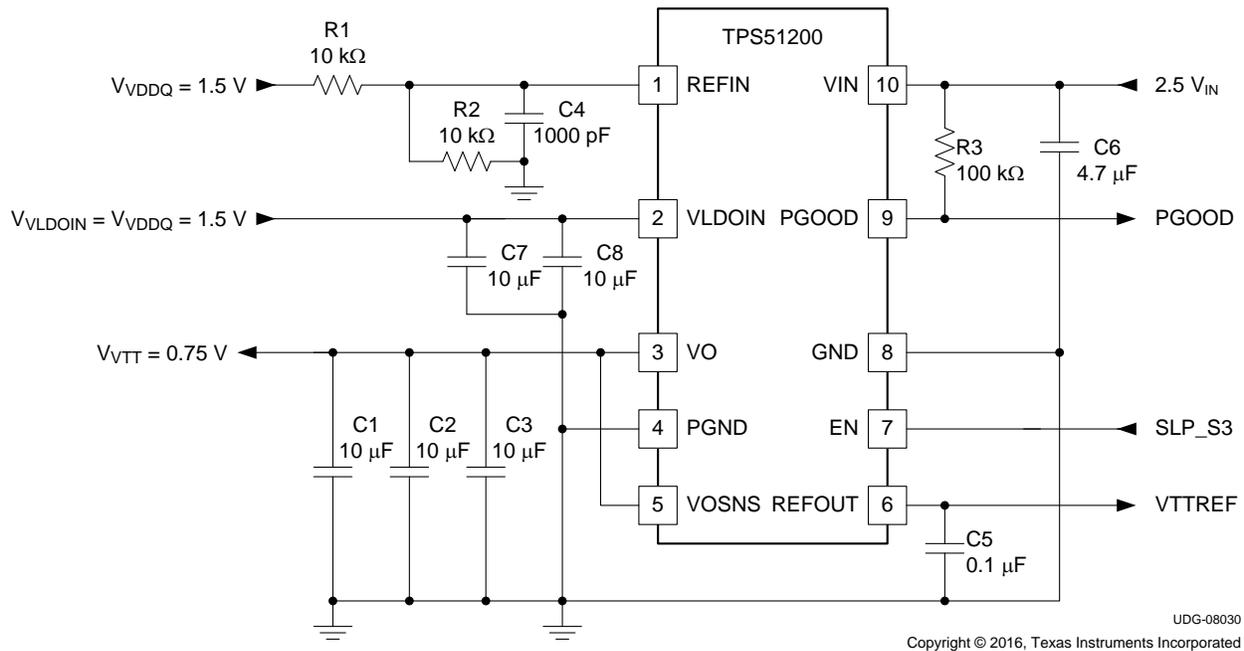


Figure 25. 2.5-V<sub>IN</sub>, DDR3 Configuration

Table 3. 2.5-V<sub>IN</sub>, DDR3 Configuration List of Materials

REFERENCE DESIGNATOR	DESCRIPTION	SPECIFICATION	PART NUMBER	MANUFACTURER
R1, R2	Resistor	10 kΩ		
R3		100 kΩ		
C1, C2, C3	Capacitor	10 µF, 6.3 V	GRM21BR70J106KE76L	Murata
C4		1000 pF		
C5		0.1 µF		
C6		4.7 µF, 6.3 V	GRM21BR60J475KA11L	Murata
C7, C8		10 µF, 6.3 V	GRM21BR70J106KE76L	Murata

### 8.3.3 3.3-V<sub>IN</sub>, LP DDR3 or DDR4 Configuration

This design example describes a 3.3-V<sub>IN</sub>, LP DDR3 or DDR4 configuration application.

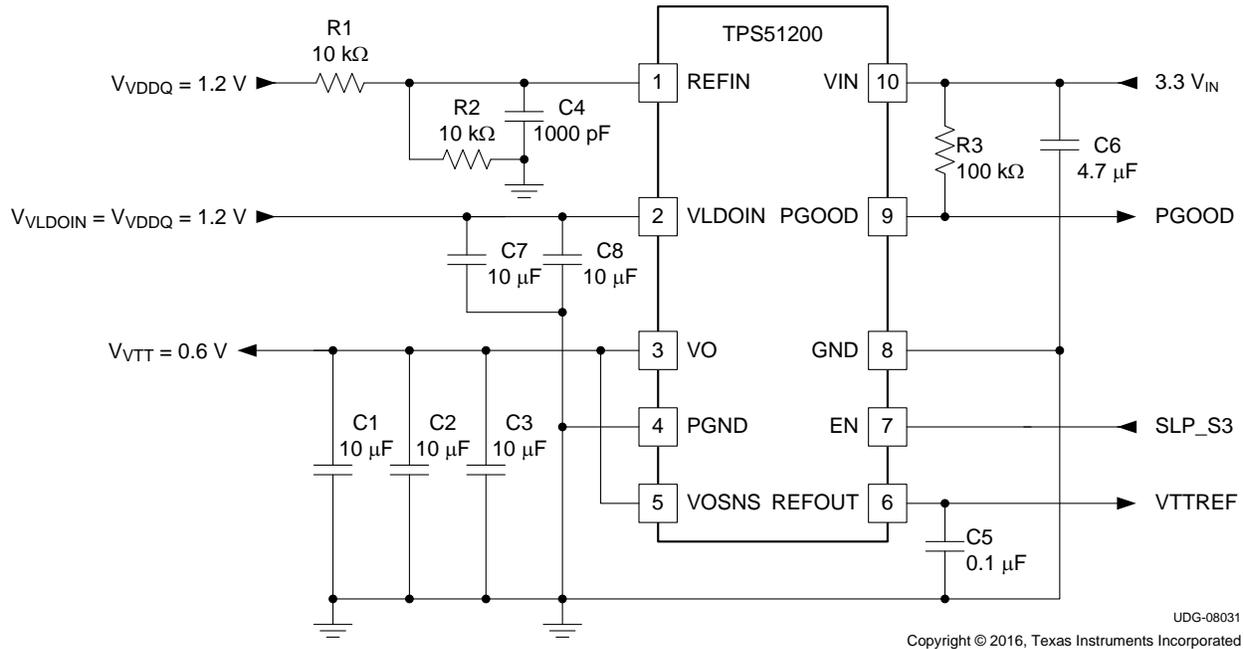


Figure 26. 3.3-V<sub>IN</sub>, LP DDR3 or DDR4 Configuration

Table 4. 3.3-V<sub>IN</sub>, LP DDR3 or DDR4 Configuration List of Materials

REFERENCE DESIGNATOR	DESCRIPTION	SPECIFICATION	PART NUMBER	MANUFACTURER
R1, R2	Resistor	10 kΩ		
R3		100 kΩ		
C1, C2, C3	Capacitor	10 µF, 6.3 V	GRM21BR70J106KE76L	Murata
C4		1000 pF		
C5		0.1 µF		
C6		4.7 µF, 6.3 V	GRM21BR60J475KA11L	Murata
C7, C8		10 µF, 6.3 V	GRM21BR70J106KE76L	Murata

### 8.3.4 3.3-V<sub>IN</sub>, DDR3 Tracking Configuration

This design example describes a 3.3-V<sub>IN</sub>, DDR3 tracking configuration application.

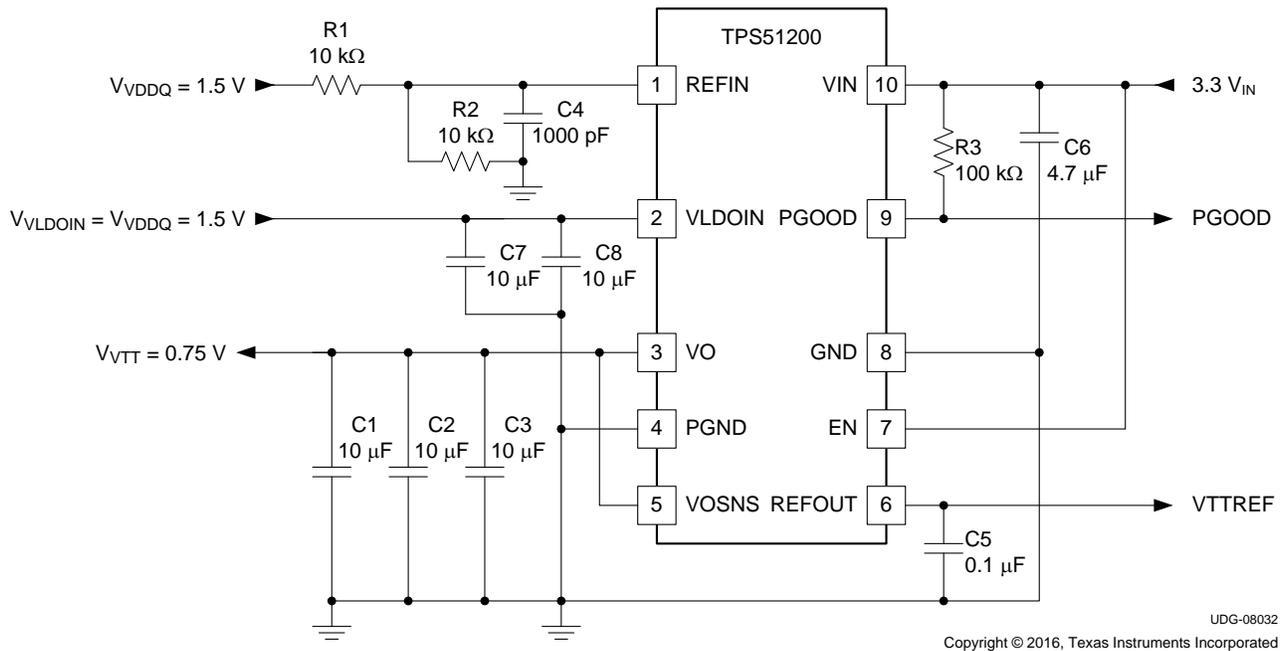


Figure 27. 3.3-V<sub>IN</sub>, DDR3 Tracking Configuration

Table 5. 3.3-V<sub>IN</sub>, DDR3 Tracking Configuration List of Materials

REFERENCE DESIGNATOR	DESCRIPTION	SPECIFICATION	PART NUMBER	MANUFACTURER
R1, R2	Resistor	10 kΩ		
R3		100 kΩ		
C1, C2, C3	Capacitor	10 µF, 6.3 V	GRM21BR70J106KE76L	Murata
C4		1000 pF		
C5		0.1 µF		
C6		4.7 µF, 6.3 V	GRM21BR60J475KA11L	Murata
C7, C8		10 µF, 6.3 V	GRM21BR70J106KE76L	Murata

### 8.3.5 3.3-V<sub>IN</sub>, LDO Configuration

This design example describes a 3.3-V<sub>IN</sub>, LDO configuration application.

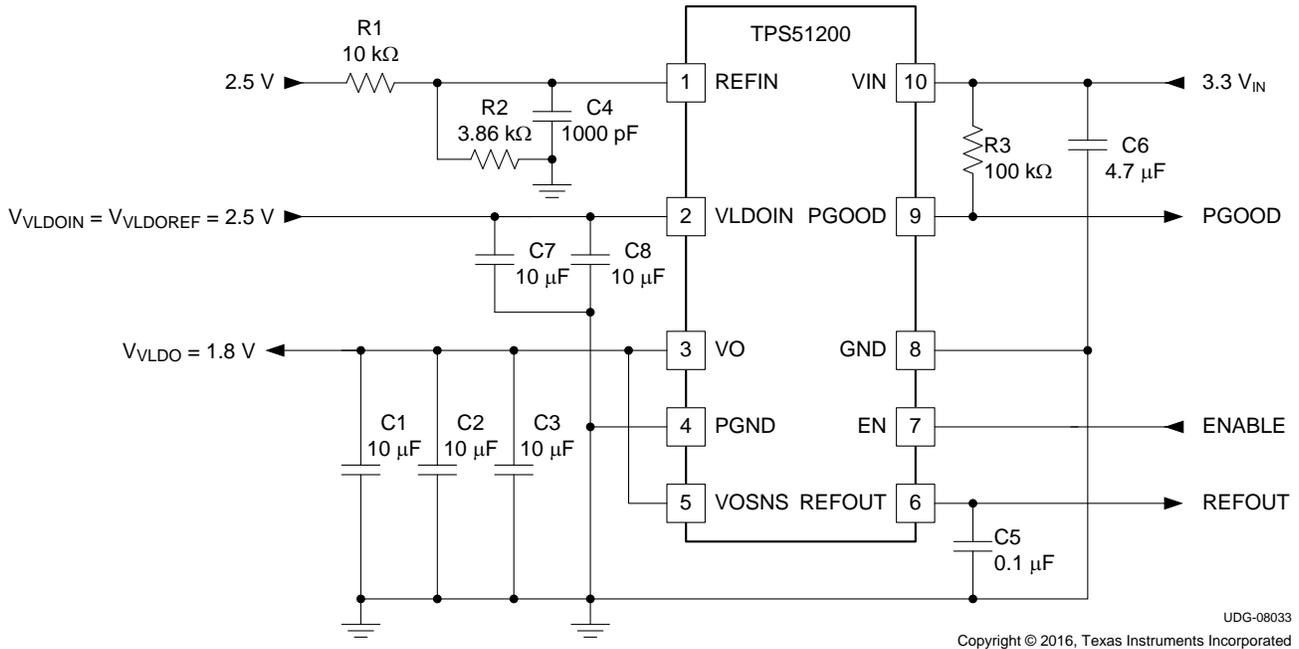


Figure 28. 3.3-V<sub>IN</sub>, LDO Configuration

Table 6. 3.3-V<sub>IN</sub>, LDO Configuration List of Materials

REFERENCE DESIGNATOR	DESCRIPTION	SPECIFICATION	PART NUMBER	MANUFACTURER
R1	Resistor	3.86 kΩ		
R2		10 kΩ		
R3		100 kΩ		
C1, C2, C3	Capacitor	10 μF, 6.3 V	GRM21BR70J106KE76L	Murata
C4		1000 pF		
C5		0.1 μF		
C6		4.7 μF, 6.3 V	GRM21BR60J475KA11L	Murata
C7, C8		10 μF, 6.3 V	GRM21BR70J106KE76L	Murata

### 8.3.6 3.3-V<sub>IN</sub>, DDR3 Configuration with LFP

This design example describes a 3.3-V<sub>IN</sub>, DDR3 configuration with LFP application.

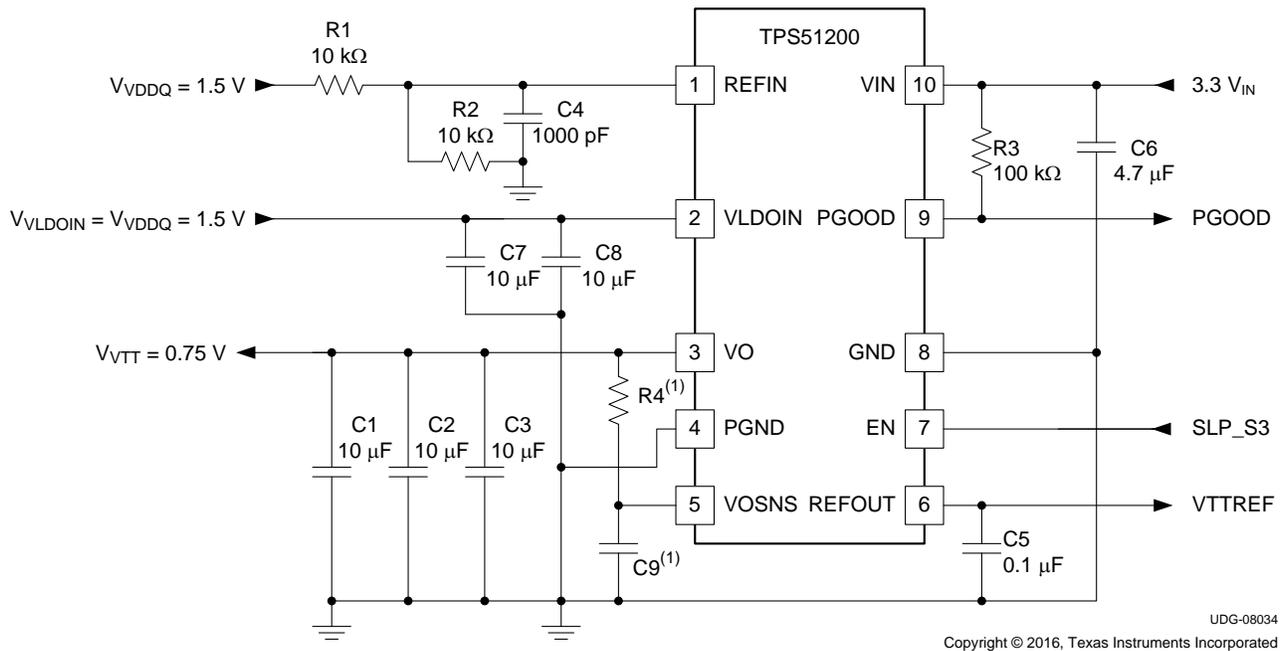


Figure 29. 3.3-V<sub>IN</sub>, DDR3 Configuration with LFP

Table 7. 3.3-V<sub>IN</sub>, DDR3 Configuration with LFP List of Materials

REFERENCE DESIGNATOR	DESCRIPTION	SPECIFICATION	PART NUMBER	MANUFACTURER
R1, R2	Resistor	10 kΩ		
R3		100 kΩ		
R4 <sup>(1)</sup>				
C1, C2, C3	Capacitor	10 μF, 6.3 V	GRM21BR70J106KE76L	Murata
C4		1000 pF		
C5		0.1 μF		
C6		4.7 μF, 6.3 V	GRM21BR60J475KA11L	Murata
C7, C8		10 μF, 6.3 V	GRM21BR70J106KE76L	Murata
C9 <sup>(1)</sup>				

(1) Choose values for R4 and C9 to reduce the parasitic effect of the trace (between VO and the output MLCCs) and the output capacitors (ESR and ESL).



## 9 Power Supply Recommendations

The TPS51200-EP device is designed to operate from an input bias voltage from 2.375 V to 3.5 V, with LDO input from 1.1 V to 3.5 V. Refer to [Figure 17](#) and [Figure 18](#) for recommended power-up sequence. Maintain an EN voltage equal or lower than  $V_{VIN}$  at all times. VLDOIN can ramp up earlier than VIN if the sequence in [Figure 17](#) and [Figure 18](#) cannot be used. The input supplies should be well regulated. VLDOIN decoupling capacitance

of  $2 \times 10 \mu\text{F}$  is recommended, and VIN decoupling capacitance of  $1 \times 4.7 \mu\text{F}$  is recommended.

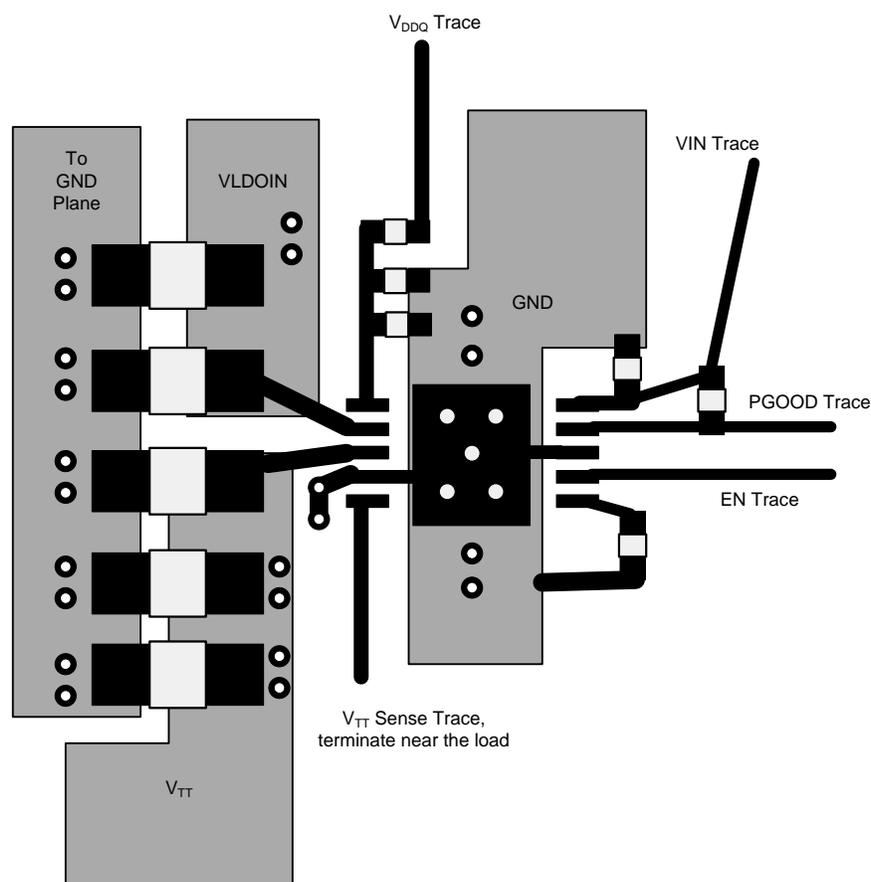
## 10 Layout

### 10.1 Layout Guidelines

Consider the following points before starting the TPS51200-EP device layout design.

- The input bypass capacitor for VLDOIN should be placed as close as possible to the pin with short and wide connections.
- The output capacitor for VO should be placed close to the pin with short and wide connection in order to avoid additional ESR and/or ESL trace inductance.
- Connect VOSNS to the positive node of each VO output capacitor as a separate trace from the high-current power line. This configuration is strongly recommended to avoid additional ESR and/or ESL. If sensing the voltage at the point of the load is required, attach each output capacitor at that point. This layout design minimizes any additional ESR and/or ESL of ground trace between the GND pin and each output capacitor.
- Consider adding low-pass filter at VOSNS if the ESR of any VO output capacitor is larger than 2 m $\Omega$ .
- REFIN can be connected separately from VLDOIN. Remember that this sensing potential is the reference voltage of REFOUT. Avoid any noise-generating lines.
- Tie the negative node of each VO output capacitor to the REFOUT capacitor by avoiding common impedance to the high current path of the VO source and sink current.
- The GND and PGND pins should be connected to the thermal land underneath the die pad with multiple vias connecting to the internal system ground planes (for better result, use at least two internal ground planes). Use as many vias as possible to reduce the impedance between PGND or GND and the system ground plane. Also, place bulk capacitors close to the DIMM load point, route the VOSNS to the DIMM load sense point.
- In order to effectively remove heat from the package, properly prepare the thermal land. Apply solder directly to the thermal pad. The wide traces of the component and the side copper connected to the thermal land pad help to dissipate heat. Connected the numerous vias that are 0.33 mm in diameter from the thermal land to any internal and solder-side ground plane to increase dissipation.
- Consult the TPS51200-EP-EVM User's Guide ([SLUU323](#)) for detailed layout recommendations.

## 10.2 Layout Example



**Figure 30. Layout Recommendation**

## 10.3 Thermal Design Considerations

Because the TPS51200-EP is a linear regulator, the VO current flows in both source and sink directions, thereby dissipating power from the device. When the device is sourcing current, the voltage difference shown in Equation 4 calculates the power dissipation.

$$P_{D\_SRC} = (V_{VLDOIN} - V_{VO}) \times I_{O\_SRC} \quad (4)$$

In this case, if the VLDOIN pin is connected to an alternative power supply lower than the VDDQ voltage, overall power loss can be reduced. During the sink phase, the device applies the VO voltage across the internal LDO regulator. Equation 5 calculates the power dissipation, PD\_SNK.

$$P_{D\_SNK} = V_{VO} \times I_{SNK} \quad (5)$$

Because the device does not sink and source current at the same time and the I/O current may vary rapidly with time, the actual power dissipation should be the time average of the above dissipations over the thermal relaxation duration of the system. The current used for the internal current control circuitry from the VIN supply and the VLDOIN supply are other sources of power consumption. This power can be estimated as 5 mW or less during normal operating conditions and must be effectively dissipated from the package.

## Thermal Design Considerations (continued)

Maximum power dissipation allowed by the package is calculated by [Equation 6](#).

$$P_{PKG} = \frac{T_{J(max)} - T_{A(max)}}{\theta_{JA}}$$

where

- $T_{J(max)}$  is 125°C.
- $T_{A(max)}$  is the maximum ambient temperature in the system.
- $\theta_{JA}$  is the thermal resistance from junction to ambient.

### NOTE

Because [Equation 6](#) demonstrates the effects of heat spreading in the ground plane, use it as a guideline only. Do not use [Equation 6](#) to estimate actual thermal performance in real application environments.

In an application where the device is mounted on PCB, TI strongly recommends using  $\psi_{JT}$  and  $\psi_{JB}$ , as explained in the section pertaining to estimating junction temperature in the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#). Using the thermal metrics  $\psi_{JT}$  and  $\psi_{JB}$ , as shown in the [Thermal Information](#) table, estimate the junction temperature with corresponding formulas shown in [Equation 7](#). The older  $\theta_{JC}$  top parameter specification is listed as well for the convenience of backward compatibility.

$$T_J = T_T + \Psi_{JT} \times P_D \tag{7}$$

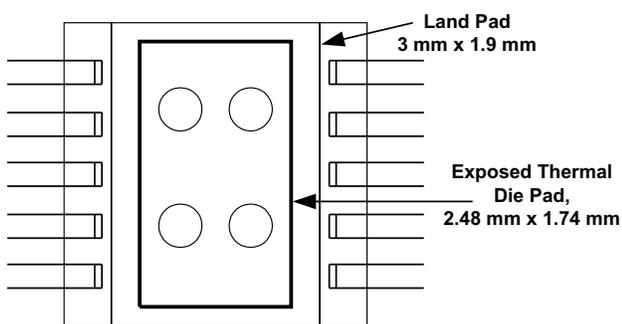
$$T_J = T_B + \Psi_{JB} \times P_D$$

where

- $P_D$  is the power dissipation shown in [Equation 4](#) and [Equation 5](#).
- $T_T$  is the temperature at the center-top of the IC package.
- $T_B$  is the PCB temperature measured 1-mm away from the thermal pad package on the PCB surface (see [Figure 32](#)).

### NOTE

Both  $T_T$  and  $T_B$  can be measured on actual application boards using a thermo-gun (an infrared thermometer). For more information about measuring  $T_T$  and  $T_B$ , see the application report *Using New Thermal Metrics* ([SBVA025](#)).



UDG-08018

Figure 31. Recommended Land Pad Pattern

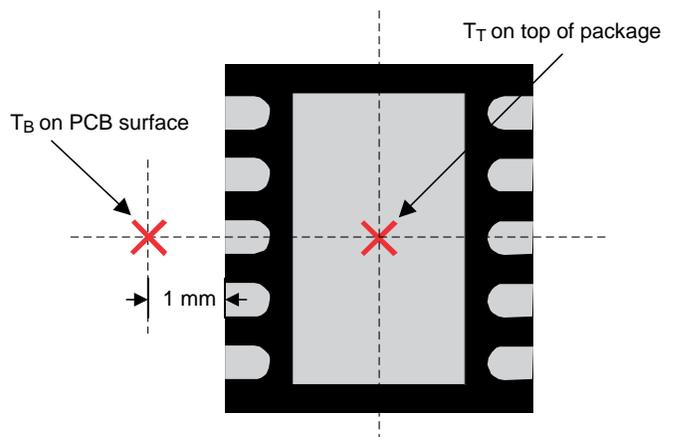


Figure 32. Package Thermal Measurement

## 11 デバイスおよびドキュメントのサポート

### 11.1 デバイス・サポート

#### 11.1.1 デベロッパー・ネットワークの製品に関する免責事項

デベロッパー・ネットワークの製品またはサービスに関するTIの出版物は、単独またはTIの製品、サービスと一緒に提供される場合に関係なく、デベロッパー・ネットワークの製品またはサービスの適合性に関する是認、デベロッパー・ネットワークの製品またはサービスの是認の表明を意味するものではありません。

#### 11.1.2 開発サポート

##### 11.1.2.1 評価モジュール

TPS51200-EPデバイスを使用する回路の初期パフォーマンス評価に役立てるため、評価モジュール(EVM)を利用可能です。[TPS51200-EPEVM](#)評価モジュールと、対応のユーザー・ガイド([SLUU323](#))は、テキサス・インスツルメンツのWebサイトにある製品フォルダで請求するか、[TI eStore](#)から直接購入できます。

##### 11.1.2.2 SPICEモデル

SPICEを使用した回路パフォーマンスのコンピュータによるシミュレーションは、アナログ回路やシステムのパフォーマンスを分析するため多くの場合に有用です。TPS51200-EPデバイス用のSPICEモデルは、[ここ](#)で入手できます。

### 11.2 ドキュメントのサポート

#### 11.2.1 関連資料

- 『新しい熱測定基準の使用』、[SBVA025](#)
- 『半導体およびICパッケージの熱指標』、[SPRA953](#)
- 『TPS51200-EP EVMシンクソースDDR終端レギュレータの使用』、[SLUU323](#)
- TPS51100デバイスの詳細については、[ti.com](#)にある製品フォルダを参照してください。

#### 11.3 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、[ti.com](#)のデバイス製品フォルダを開いてください。右上の隅にある「通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

#### 11.4 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At [e2e.ti.com](#), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 11.5 商標

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#### 11.6 静電気放電に関する注意事項



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## 11.7 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。これらの情報は、指定のデバイスに対して提供されている最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS51200MDRCTEP	ACTIVE	VSON	DRC	10	250	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-55 to 125	1200M	<b>Samples</b>
V62/16610-01XE	ACTIVE	VSON	DRC	10	250	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-55 to 125	1200M	<b>Samples</b>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## GENERIC PACKAGE VIEW

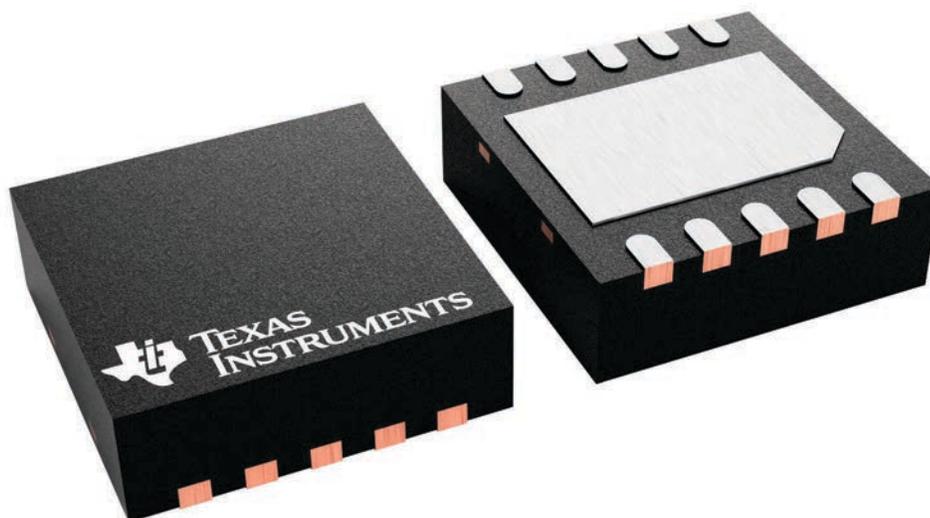
**DRC 10**

**VSON - 1 mm max height**

3 x 3, 0.5 mm pitch

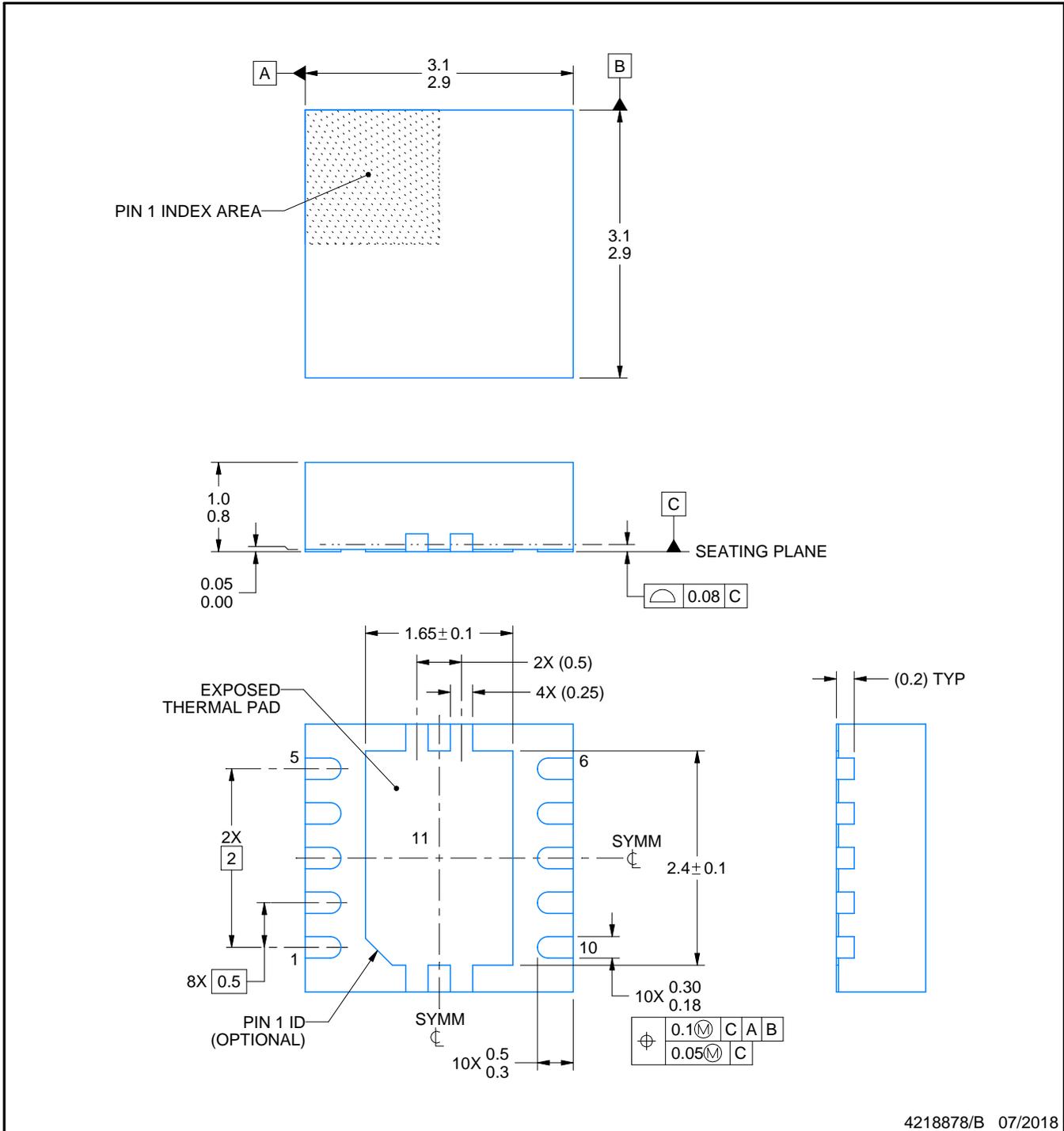
PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



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NOTES:

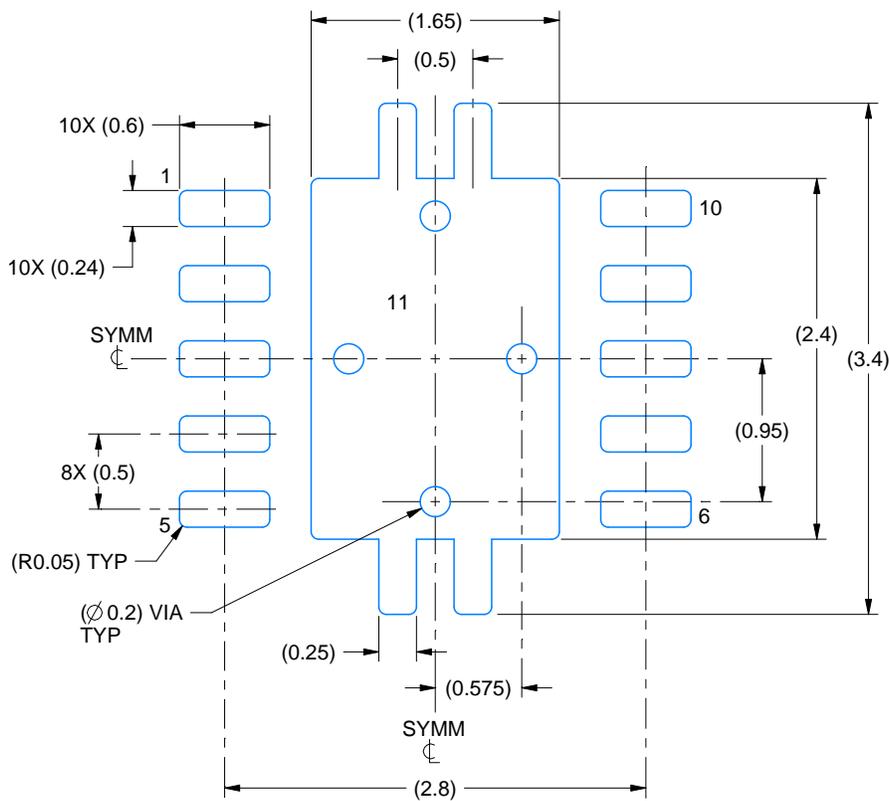
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

# EXAMPLE BOARD LAYOUT

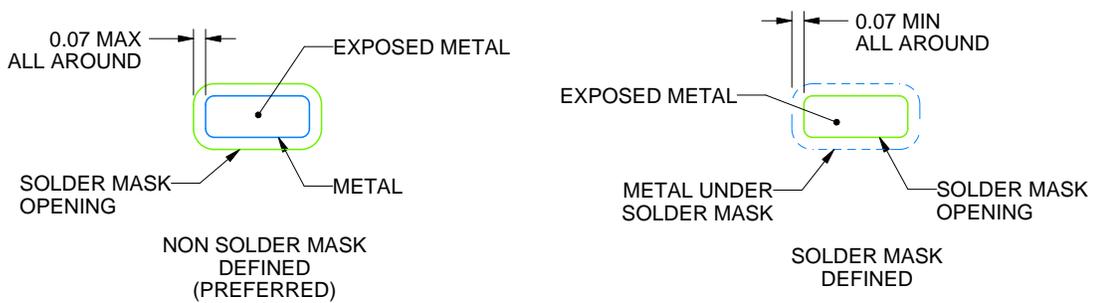
DRC0010J

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:20X



SOLDER MASK DETAILS

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NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/sluea271](http://www.ti.com/lit/sluea271)).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



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